

深圳市晶泰源电子有限公司

MMBT3904 TRANSISTOR (NPN)

FEATURES

- As complementary type the PNP transistor MMBT3906 is recommended
- Epitaxial planar die construction

MARKING: 1AM

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	200	mA
P_C	Total Device Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	625	$^{\circ}\text{C}/\text{W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55 to +150	$^{\circ}\text{C}$

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C=10\mu\text{A}, I_E=0$	60		V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=1\text{mA}, I_B=0$	40		V
Emitter-base breakdown voltage	V_{EBO}	$I_E=10\mu\text{A}, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$		0.1	μA
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}, V_{BE(off)}=3\text{V}$		50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100	400	
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=50\text{mA}$	60		
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$		0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300		MHz
Delay Time	t_d	$V_{CC}=3\text{V}, V_{BE}=-0.5\text{V}$		35	nS
Rise Time	t_r	$I_C=10\text{mA}, I_{B1}=-I_{B2}=1.0\text{mA}$		35	nS
Storage Time	t_s	$V_{CC}=3\text{V}, I_C=10\text{mA}$,		200	nS
Fall Time	t_f	$I_{B1}=-I_{B2}=1\text{mA}$		50	nS

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	G
Range	100-200	200-300	300-400